

IN THE CLAIMS

Please amend the following claims:

Sub
C1
B1

30. (Currently amended) A method of forming a semiconductor device comprising:

- forming a gate electrode having a first thickness on a gate dielectric layer formed on a first surface of a substrate;
- forming a pair of source/drain regions on opposite sides of the gate electrode;
- forming a silicon germanium film having a second thickness on the gate electrode;
- forming a silicon germanium film having the second thickness on the source/drain regions;

and

- forming a silicide layer having a third thickness on the silicon germanium films[.];
- forming a pair of sidewall spacers having a first height above the substrate surface on opposite sides of the gate electrode, wherein the first height is greater than the sum of the first and second and third thicknesses.

31. (Cancelled) The method of claim 30 further comprising:

- forming a pair of sidewall spacers having a first height above the substrate surface on opposite sides of the gate electrode, wherein the first height is greater than the sum of the first and second and third thicknesses.

32. (Original) The method of claim 31, wherein the sidewall spacers comprise silicon nitride.

33. (Cancelled) A method of forming a semiconductor device, comprising:

- forming an isolation region having a top surface in a semiconductor substrate;
- etching the semiconductor substrate adjacent to the isolation region to form a recess region;
- depositing a silicon germanium film having a top surface in the recessed region; and
- depositing a silicide layer having a top surface over the silicon germanium film.

34. (Cancelled) The method of forming a semiconductor device of claim 33, wherein the silicide layer top surface extends above the isolation region top surface.

35. (Cancelled) The method of forming a semiconductor device of claim 34,
wherein
the silicon germanium film top surface extends above the isolation region top surface.

36. (New) The method of claim 30 wherein the gate electrode comprises
polysilicon.

37. (New) The method of claim 30 wherein the sidewall spacers are less than
300Å in width.

P1
(Cont'd)